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(54) **SOLID-STATE IMAGING DEVICE AND ELECTRONIC DEVICE**

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(71) Applicant: **SONY SEMICONDUCTOR SOLUTIONS CORPORATION**, Kanagawa (JP)

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(72) Inventor: **Tatsuya OKAWA**, Kanagawa (JP)

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(73) Assignee: **SONY SEMICONDUCTOR SOLUTIONS CORPORATION**, Kanagawa (JP)

(57) **ABSTRACT**

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Color mixing between pixels of different colors is suppressed. A solid-state imaging device includes: a semiconductor layer including a plurality of photoelectric conversion sections partitioned by an isolation region; a shared on-chip lens arranged on a light incident surface side of the semiconductor layer, the shared on-chip lens being shared by the photoelectric conversion sections adjacent to each other with the isolation region interposed between the photoelectric conversion sections, and having a condensing point positioned in the isolation region; and a concave portion provided in an upper portion of the photoelectric conversion sections that share the shared on-chip lens on the light incident surface of the semiconductor layer.

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